



SEMICONDUCTOR

GPRC

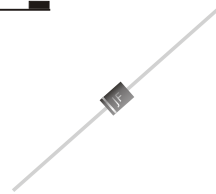
## EGP10ATHRU EGP10M

SUPER FAST RECTIFIER  
Reverse Voltage: 50 to 1000 Volts  
Forward Current: 1.0Ampere

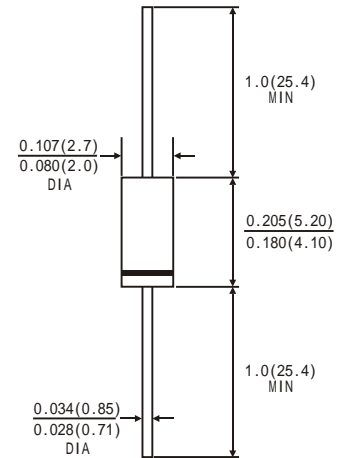
SILICON RECTIFIER

## FEATURES

- GPRC( Glass Passivated Rectifier Chip) inside
- Glass passivated cavity-free junction
- Low forward voltage drop,High current capability
- High surge current capability
- Super fast recovery time
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0



## DO-41



## MECHANICAL DATA

- Case: JEDEC DO-41 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750,method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.012ounce, 0.34 gram

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Rating at 25 °C ambient temperature unless otherwise specified ,Single phase ,half wave ,60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

	Symbols	EGP 10A	EGP 10B	EGP 10D	EGP 10F	EGP 10G	EGP 10J	EGP 10K	EGP 10M	Units	
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	150	200	400	600	800	1000	Volts	
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	105	140	280	280	280	280	Volts	
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	150	200	400	600	800	1000	Volts	
Maximum Average Forward Rectified Current 0.375"(9.5mm)lead Length at T <sub>a</sub> =55 °C	I(AV)	1.0								Amp	
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>	30.0								Amps	
Maximum Instantaneous Forward Voltage at 1.0 A	V <sub>F</sub>	0.95				1.25				Volts	
Maximum DC Reverse Current At Rated DC Blocking Voltage	T <sub>A</sub> =25 °C	5.0								μA	
	T <sub>A</sub> =100 °C	50									
Maximum Reverse Recovery Time(Note1)	T <sub>rr</sub>	35								ns	
Typical Junction Capacitance(Note2)	C <sub>J</sub>	50					25				PF
Operating Junction and Storage Temperature Range	T <sub>J</sub>	-65 to +125								°C	
	T <sub>STG</sub>	-65 to +150									

Note: 1. Test conditions: I<sub>F</sub>=0.5A, I<sub>R</sub>=1.0A, I<sub>RR</sub>=0.25A.

2. Measured at 1MHz and applied reverse voltage of 4.0 Volts.

# RATINGS AND CHARACTERISTIC CURVES EGP10A THRU EGP10M

FIG. 1-TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC

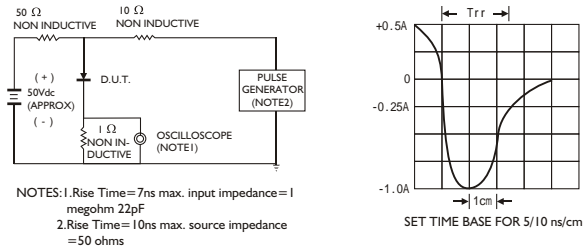


FIG. 2-TYPICAL FORWARD CURRENT DERATING CURVE

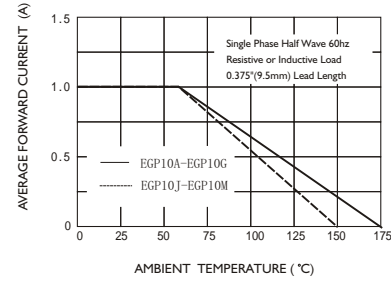


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

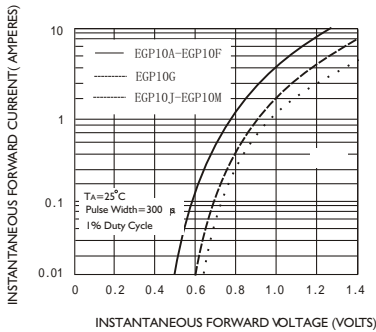


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

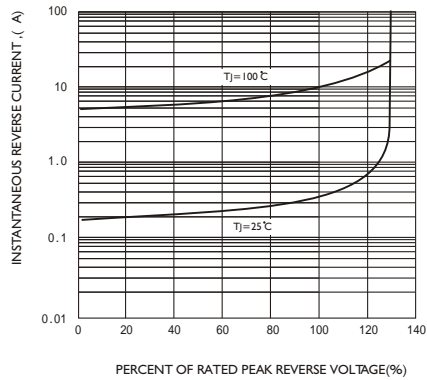


FIG. 5-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

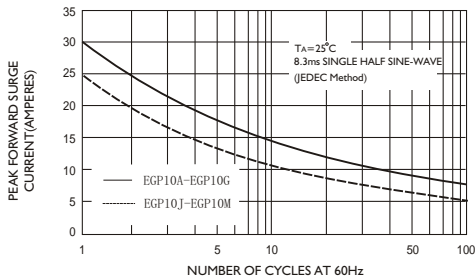


FIG. 6-TYPICAL JUNCTION CAPACITANCE

